

# 2SJ174

Silicon P-Channel MOS FET

**HITACHI**

November 1996

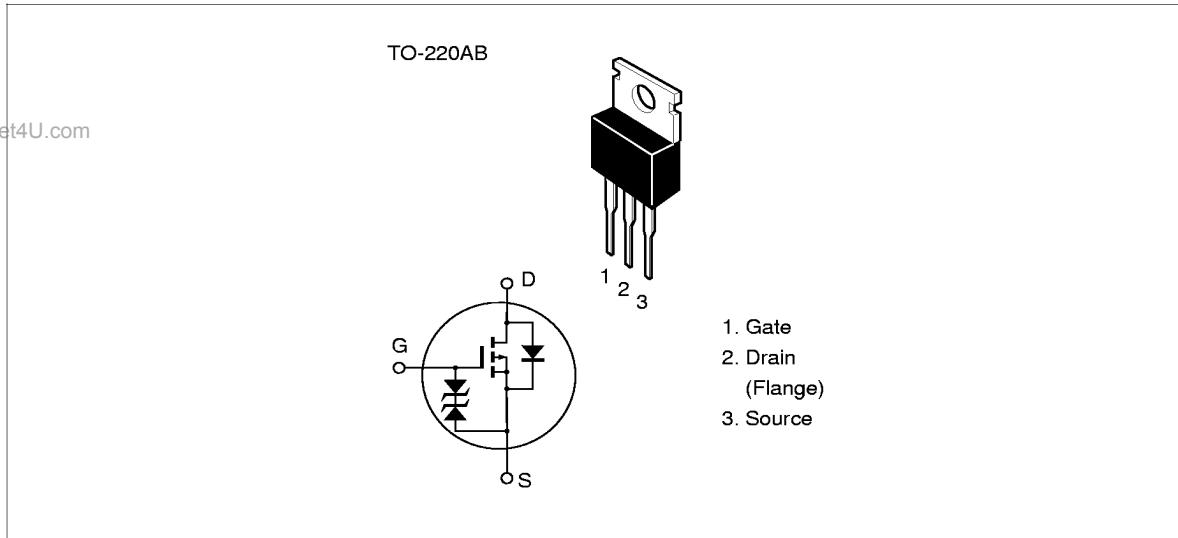
## Application

High speed power switching

## Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device
  - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

## Outline



**2SJ174****Absolute Maximum Ratings (Ta = 25°C)**

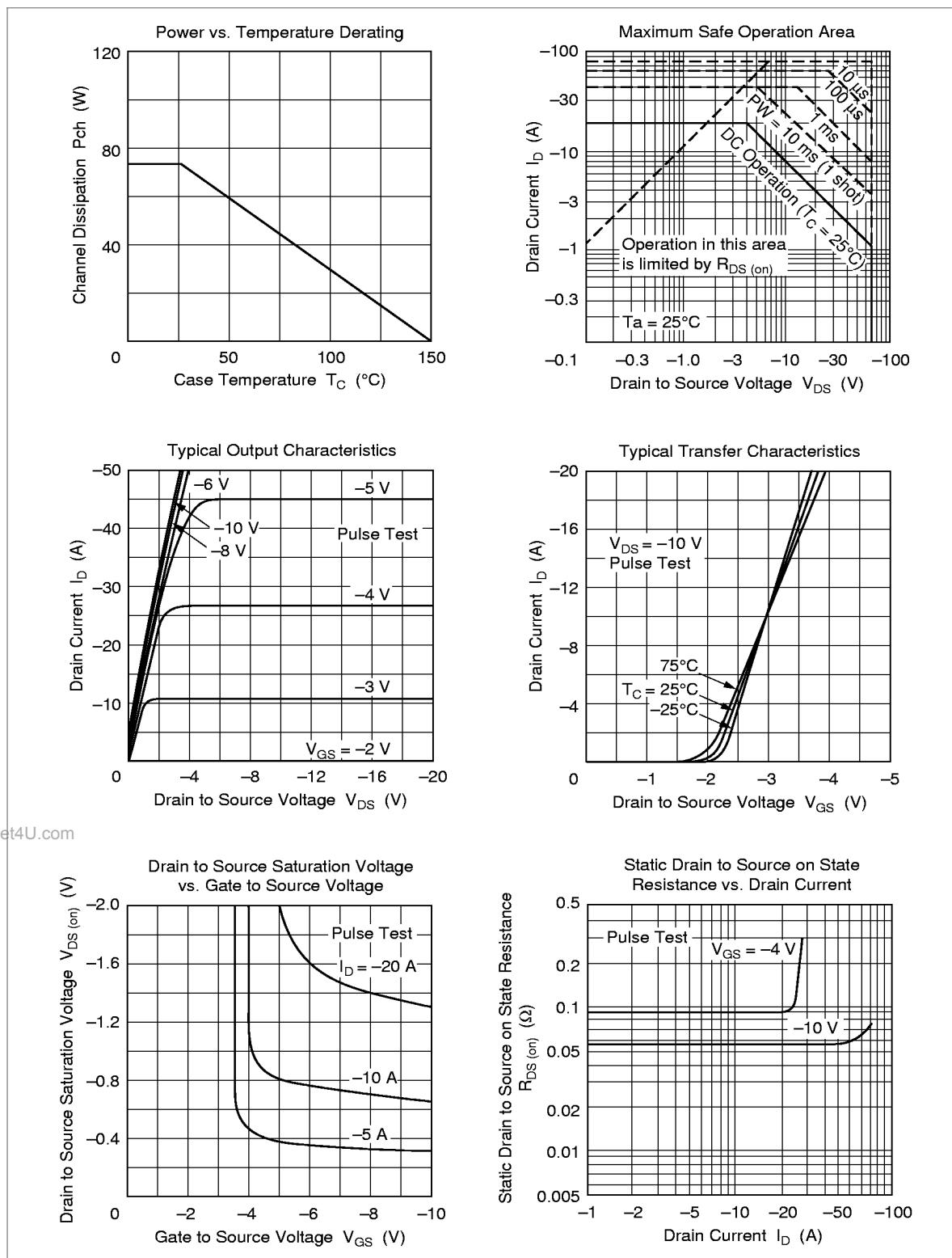
Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	-60	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	-20	A
Drain peak current	I <sub>D(pulse)</sub> <sup>*1</sup>	-80	A
Body to drain diode reverse drain current	I <sub>DR</sub>	-20	A
Channel dissipation	Pch <sup>*2</sup>	75	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

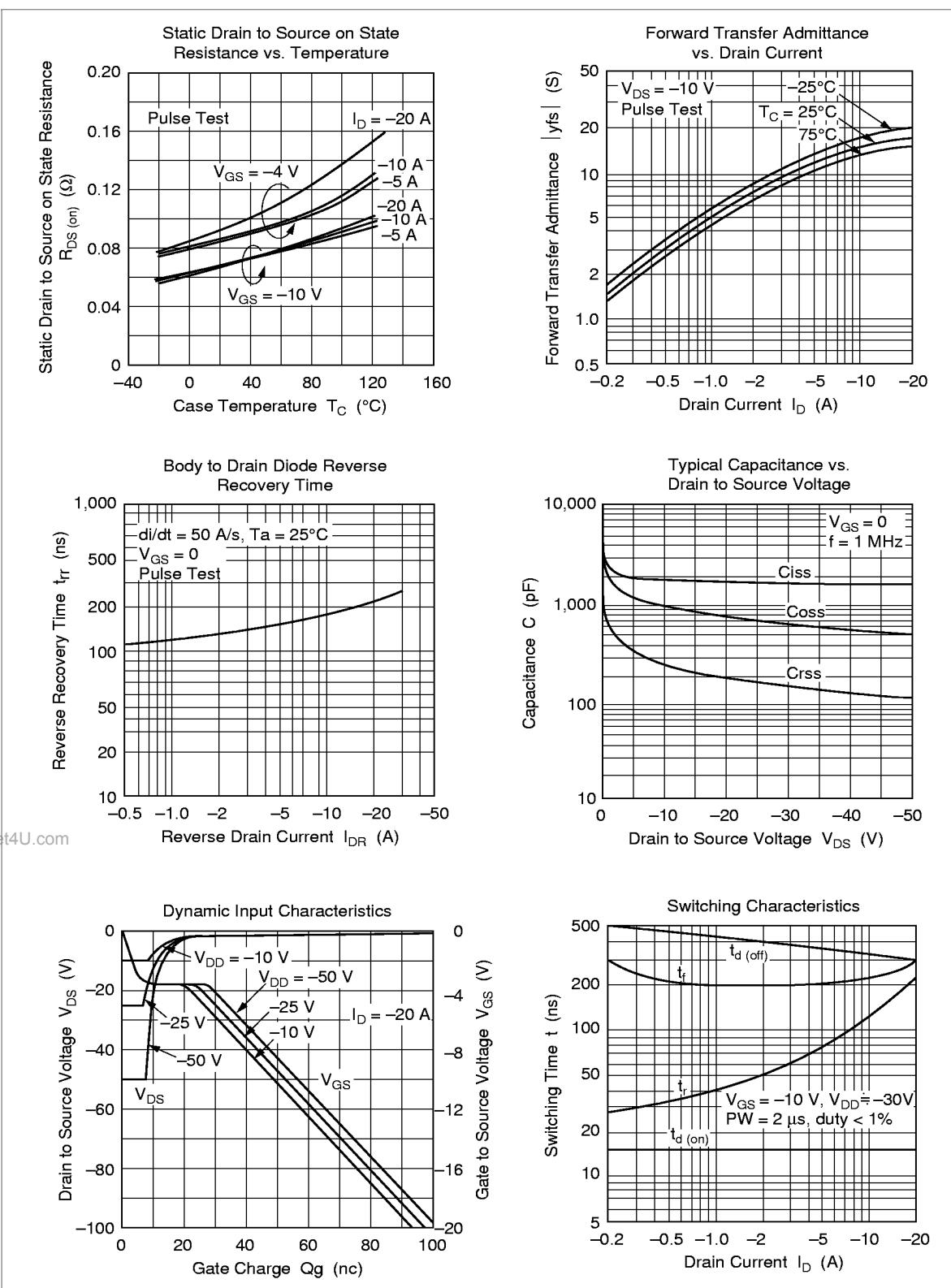
Notes 1. PW ≤ 10 μs, duty cycle ≤ 1%

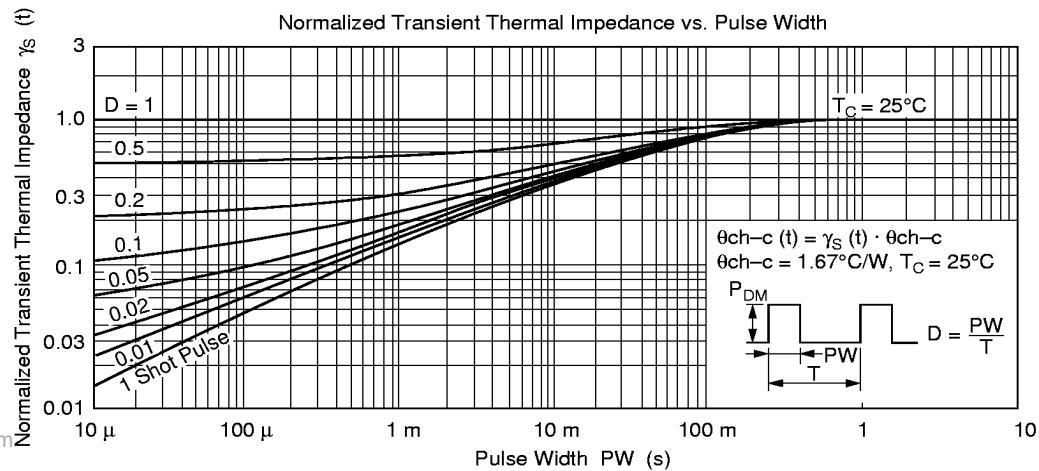
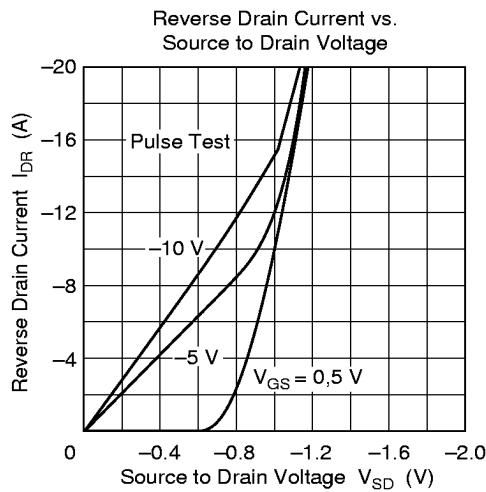
2. Value at T<sub>c</sub> = 25°C**Electrical Characteristics (Ta = 25°C)**

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	-60	—	—	V	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0
Gate to source breakdown voltage	V <sub>(BR)GSS</sub>	±20	—	—	V	I <sub>G</sub> = ±100 μA, V <sub>DS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	-250	μA	V <sub>DS</sub> = -50 V, V <sub>GS</sub> = 0
Gate to source cutoff voltage	V <sub>GS(off)</sub>	-1.0	—	-2.0	V	I <sub>D</sub> = -1 mA, V <sub>DS</sub> = -10 V
Static drain to source on state resistance	R <sub>DS(on)</sub>	—	0.065	0.085	Ω	I <sub>D</sub> = -10 A, V <sub>GS</sub> = -10 V <sup>*1</sup>
Forward transfer admittance	y <sub>fs</sub>	8	13	—	S	I <sub>D</sub> = -10 A, V <sub>DS</sub> = -10 V <sup>*1</sup>
Input capacitance	C <sub>iss</sub>	—	1850	—	pF	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0,
Output capacitance	C <sub>oss</sub>	—	990	—	pF	f = 1 MHz
Reverse transfer capacitance	C <sub>rss</sub>	—	265	—	pF	
Turn-on delay time	t <sub>d(on)</sub>	—	15	—	ns	I <sub>D</sub> = -10 A, V <sub>GS</sub> = -10 V,
Rise time	t <sub>r</sub>	—	125	—	ns	R <sub>L</sub> = 3 Ω
Turn-off delay time	t <sub>d(off)</sub>	—	345	—	ns	
Fall time	t <sub>f</sub>	—	235	—	ns	
Body to drain diode forward voltage	V <sub>DF</sub>	—	-1.2	—	V	I <sub>F</sub> = -20 A, V <sub>GS</sub> = 0
Body to drain diode reverse recovery time	t <sub>rr</sub>	—	230	—	ns	I <sub>F</sub> = -20 A, V <sub>GS</sub> = 0, di <sub>F</sub> /dt = 50 A/μs

Note 1. Pulse test

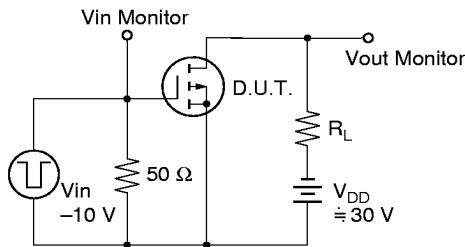
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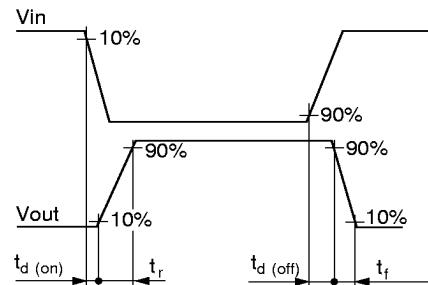
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Switching Time Test Circuit



Waveforms

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